

# TK40P04M1

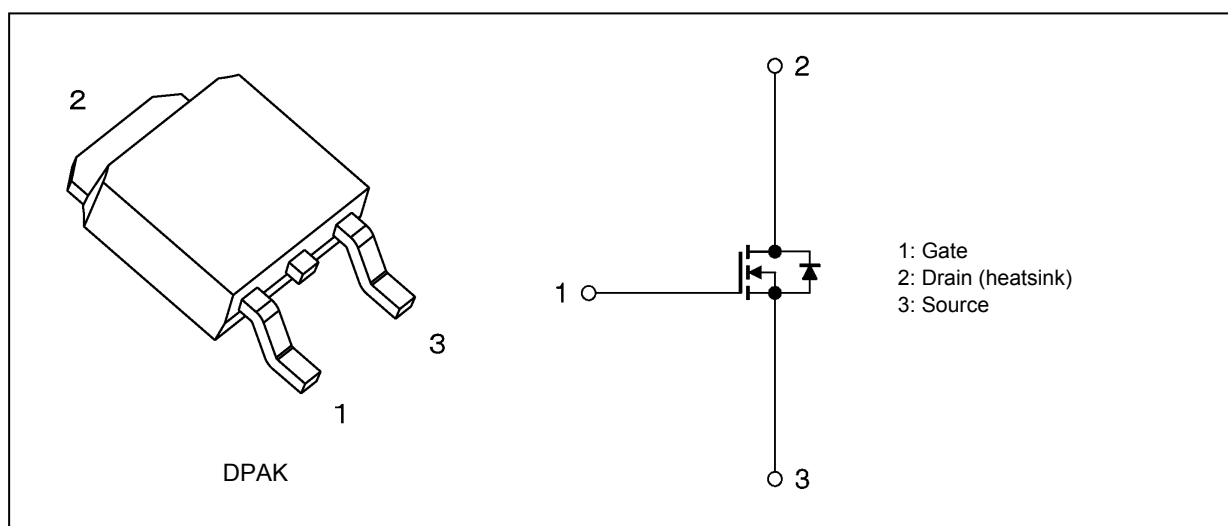
## 1. Applications

- Switching Voltage Regulators
- Motor Drivers

## 2. Features

- (1) High-speed switching
- (2) Low gate charge:  $Q_{SW} = 7.4 \text{ nC (typ.)}$
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 8.5 \text{ m}\Omega \text{ (typ.) (} V_{GS} = 10 \text{ V)}$
- (4) Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A (max) (} V_{DS} = 40 \text{ V)}$
- (5) Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V (} V_{DS} = 10 \text{ V, } I_D = 0.2 \text{ mA)}$

## 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

| Characteristics                                | Symbol    | Rating     | Unit             |
|--|-----------|------------|------------------|
| Drain-source voltage                           | $V_{DSS}$ | 40         | V                |
| Gate-source voltage                            | $V_{GSS}$ | $\pm 20$   |                  |
| Drain current (DC)                             | $I_D$     | 40         | A                |
| Drain current (pulsed)                         | $I_{DP}$  | 120        |                  |
| Power dissipation ( $T_c = 25^\circ\text{C}$ ) | $P_D$     | 47         | W                |
| Single-pulse avalanche energy                  | $E_{AS}$  | 41         | mJ               |
| Avalanche current                              | $I_{AR}$  | 40         | A                |
| Channel temperature                            | $T_{ch}$  | 150        | $^\circ\text{C}$ |
| Storage temperature                            | $T_{stg}$ | -55 to 150 |                  |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

**5. Thermal Characteristics**

| Characteristics                       | Symbol         | Max  | Unit |
|---------------------------------------|----------------|------|------|
| Channel-to-case thermal resistance    | $R_{th(ch-c)}$ | 2.65 | °C/W |
| Channel-to-ambient thermal resistance | $R_{th(ch-a)}$ | 125  |      |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 32\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 20\ \mu\text{H}$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = 40\ \text{A}$

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

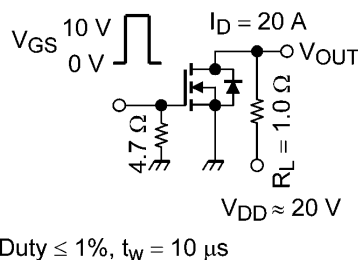
**6. Electrical Characteristics**

**6.1. Static Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                | Symbol        | Test Condition                                  | Min | Typ. | Max       | Unit             |
|--------------------------------|---------------|---|-----|------|-----------|------------------|
| Gate leakage current           | $I_{GSS}$     | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | —   | —    | $\pm 0.1$ | $\mu\text{A}$    |
| Drain cut-off current          | $I_{DSS}$     | $V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$     | —   | —    | 10        |                  |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$       | 40  | —    | —         | V                |
|                                | $V_{(BR)DSX}$ | $I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$     | 25  | —    | —         |                  |
| Gate threshold voltage         | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 0.2\text{ mA}$     | 1.3 | —    | 2.3       |                  |
| Drain-source on-resistance     | $R_{DS(ON)}$  | $V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$      | —   | 10.3 | 13.4      | $\text{m}\Omega$ |
|                                |               | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}$       | —   | 8.5  | 11        |                  |

**6.2. Dynamic Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                | Symbol    | Test Condition  | Min | Typ. | Max | Unit        |
|--------------------------------|-----------|---|-----|------|-----|-------------|
| Input capacitance              | $C_{iss}$ | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | —   | 1920 | —   | $\text{pF}$ |
| Reverse transfer capacitance   | $C_{rss}$ |   | —   | 90   | —   |             |
| Output capacitance             | $C_{oss}$ |   | —   | 310  | —   |             |
| Gate resistance                | $r_g$     | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 5\text{ MHz}$ | —   | 1.6  | 3.5 | $\Omega$    |
| Switching time (rise time)     | $t_r$     | See Figure 6.2.1.   | —   | 20   | —   | ns          |
| Switching time (turn-on time)  | $t_{on}$  |   | —   | 27   | —   |             |
| Switching time (fall time)     | $t_f$     |   | —   | 18   | —   |             |
| Switching time (turn-off time) | $t_{off}$ |   | —   | 63   | —   |             |



**Fig. 6.2.1 Switching Time Test Circuit**

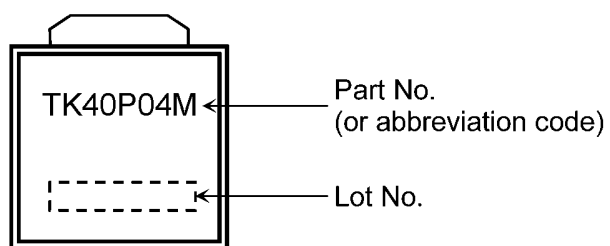
**6.3. Gate Charge Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                                 | Symbol    | Test Condition  | Min | Typ. | Max | Unit |
|---|-----------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$     | $V_{DD} \approx 32\text{ V}, V_{GS} = 10\text{ V}, I_D = 40\text{ A}$ | —   | 29   | —   | nC   |
|   |           | $V_{DD} \approx 32\text{ V}, V_{GS} = 5\text{ V}, I_D = 40\text{ A}$  | —   | 15   | —   |      |
| Gate-source charge 1                            | $Q_{gs1}$ | $V_{DD} \approx 32\text{ V}, V_{GS} = 10\text{ V}, I_D = 40\text{ A}$ | —   | 6.0  | —   |      |
| Gate-drain charge                               | $Q_{gd}$  |   | —   | 4.7  | —   |      |
| Gate switch charge                              | $Q_{sw}$  |   | —   | 7.4  | —   |      |

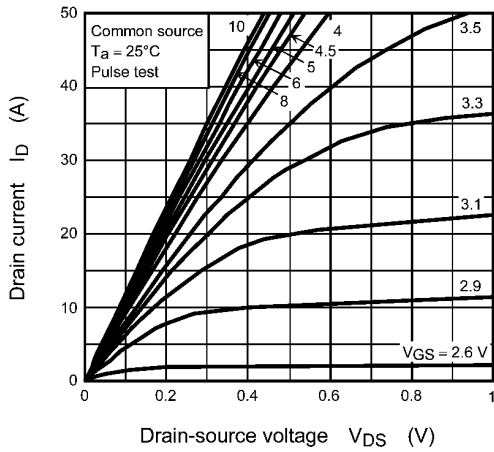
**6.4. Source-Drain Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                | Symbol             | Test Condition                              | Min | Typ. | Max  | Unit |
|--------------------------------|--------------------|---|-----|------|------|------|
| Reverse drain current (pulsed) | (Note 3) $I_{DRP}$ | —   | —   | —    | 120  | A    |
| Diode forward voltage          | $V_{DSF}$          | $I_{DR} = 40\text{ A}, V_{GS} = 0\text{ V}$ | —   | —    | -1.2 | V    |

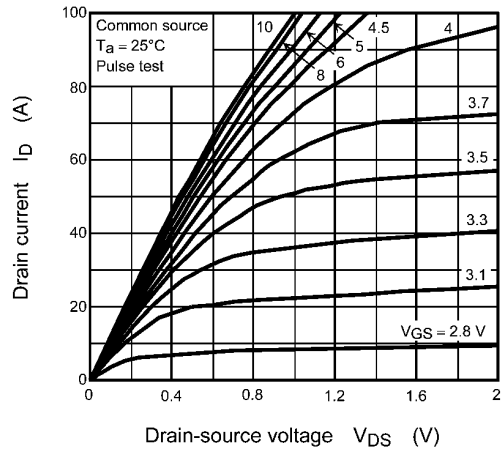
Note 3: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

**7. Marking****Fig. 7.1 Marking**

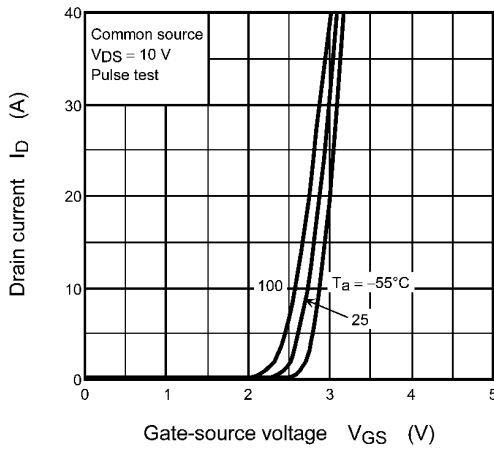
**8. Characteristics Curves (Note)**



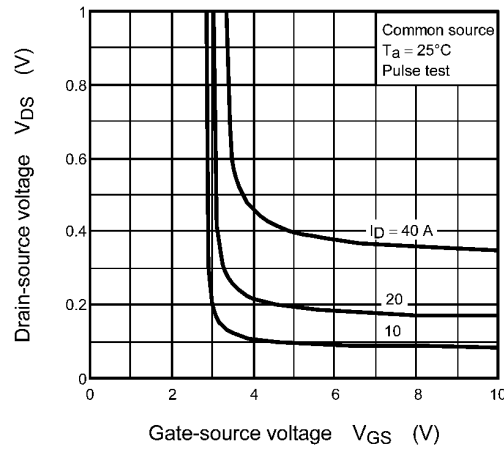
**Fig. 8.1  $I_D - V_{DS}$**



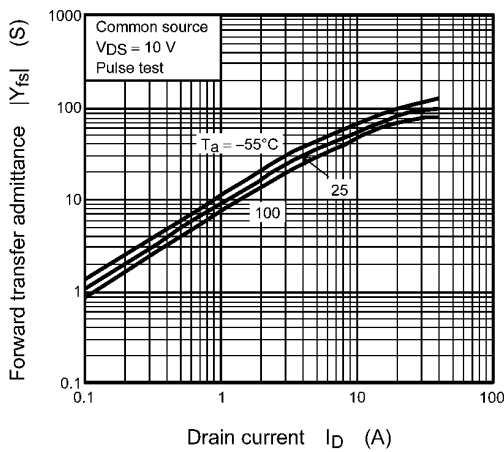
**Fig. 8.2  $I_D - V_{DS}$**



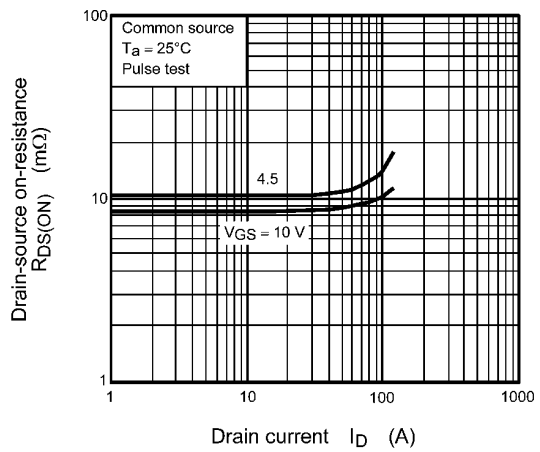
**Fig. 8.3  $I_D - V_{GS}$**



**Fig. 8.4  $V_{DS} - V_{GS}$**



**Fig. 8.5  $|Y_{fs}| - I_D$**



**Fig. 8.6  $R_{DS(ON)} - I_D$**

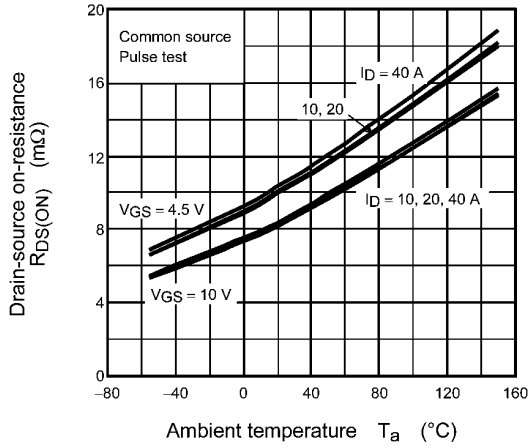


Fig. 8.7  $R_{DS(ON)} - T_a$

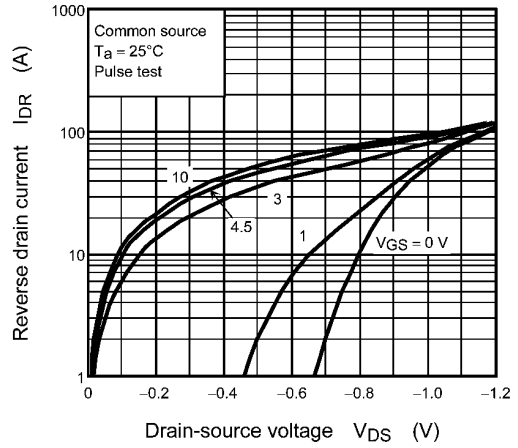


Fig. 8.8  $I_{DR} - V_{DS}$

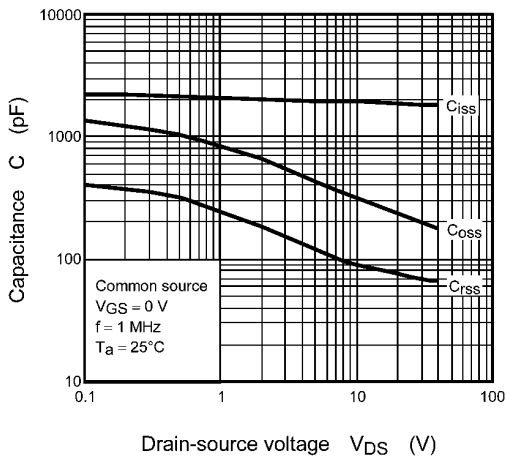


Fig. 8.9 Capacitance -  $V_{DS}$

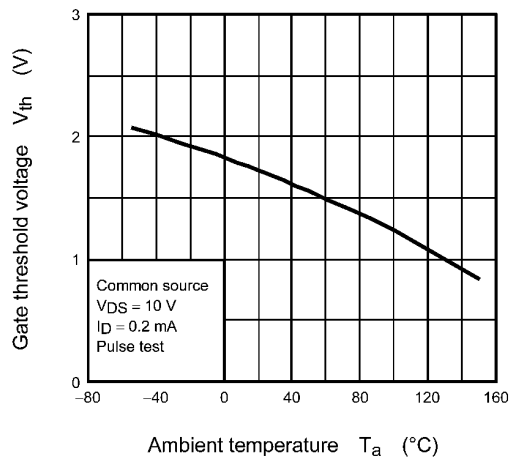


Fig. 8.10  $V_{th} - T_a$

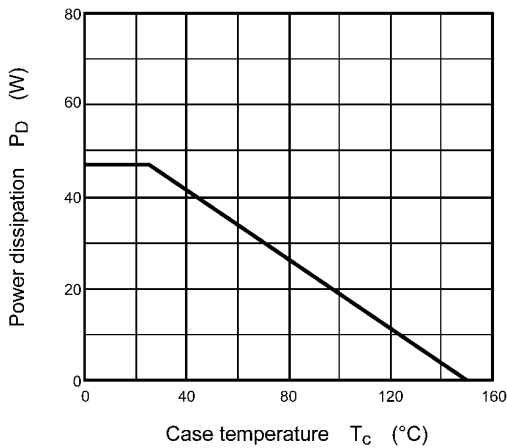


Fig. 8.11  $P_D - T_c$   
(Guaranteed Maximum)

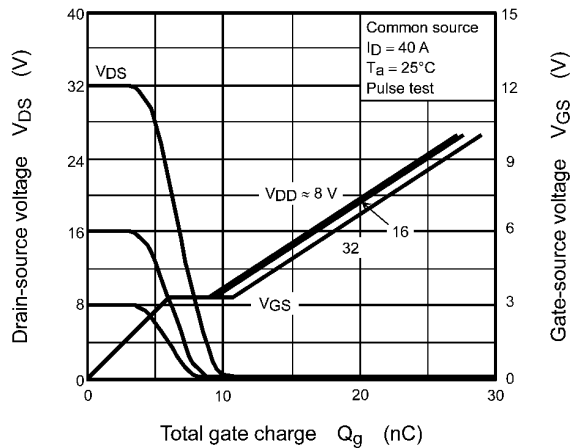
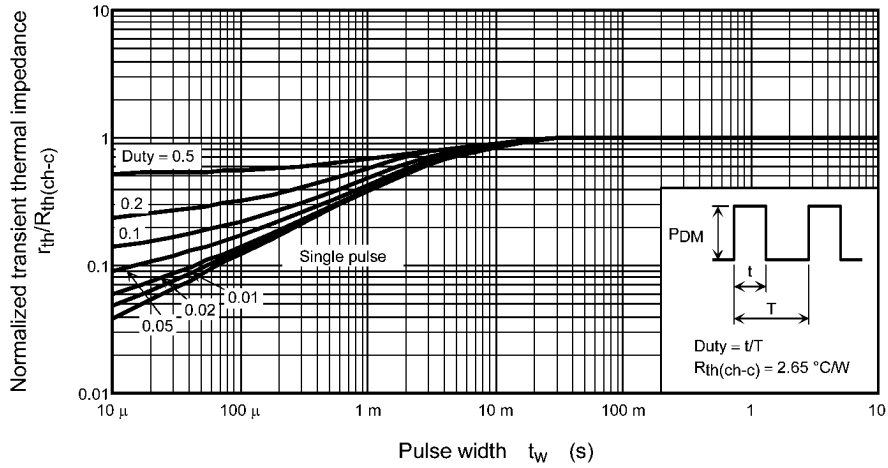
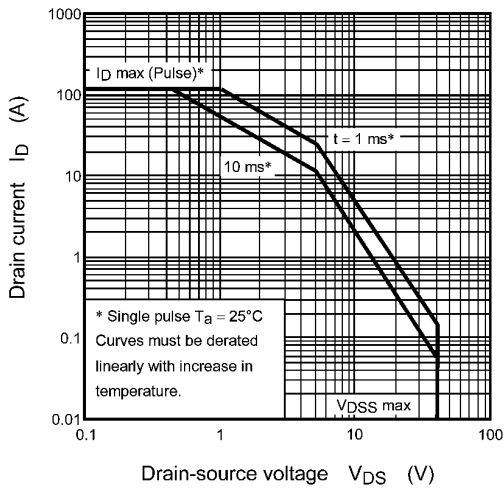


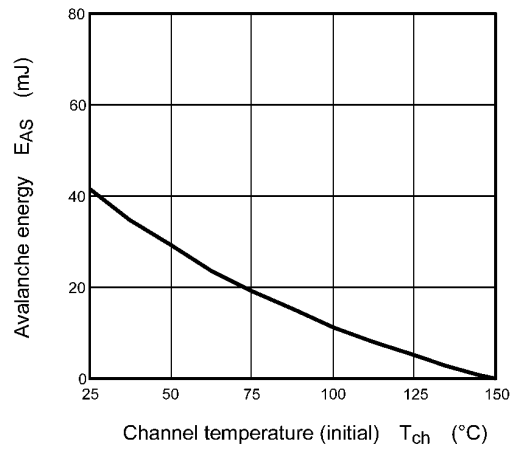
Fig. 8.12 Dynamic Input/Output Characteristics



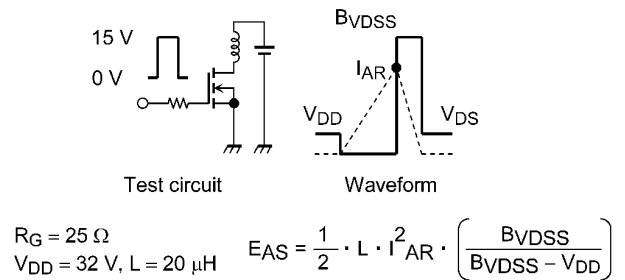
**Fig. 8.13**  $r_{th}/R_{th(ch-c)} - t_w$   
(Guaranteed Maximum)



**Fig. 8.14** Safe Operating Area  
(Guaranteed Maximum)



**Fig. 8.15**  $E_{AS} - T_{ch}$   
(Guaranteed Maximum)



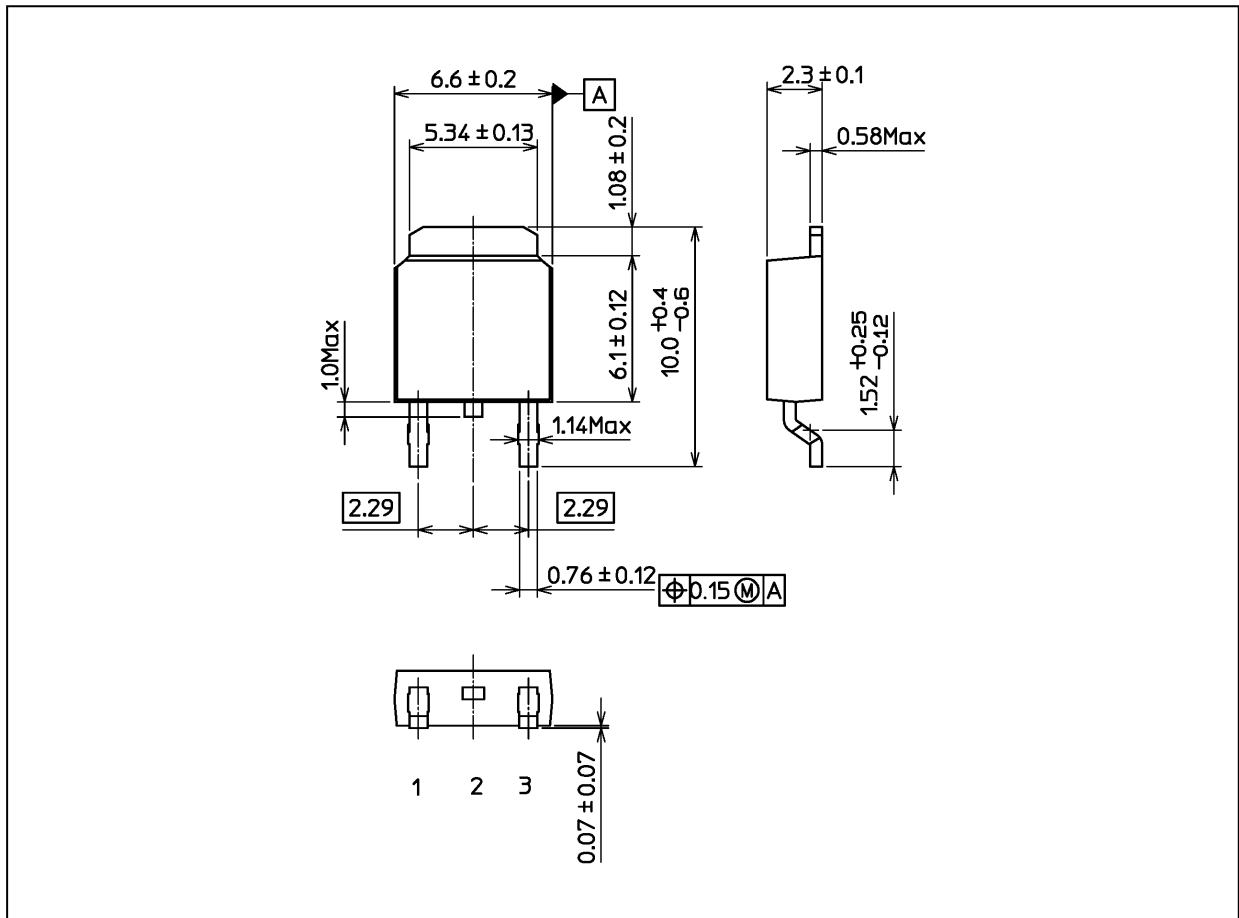
**Fig. 8.16** Test Circuit/Waveform

$$R_G = 25 \Omega, V_{DD} = 32 \text{ V}, L = 20 \mu\text{H} \quad E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left( \frac{BV_{DSS}}{BV_{DSS} - V_{DD}} \right)$$

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

| Package Name(s) |
|-----------------|
| TOSHIBA: 2-7K1S |
| Nickname: DPAK  |



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